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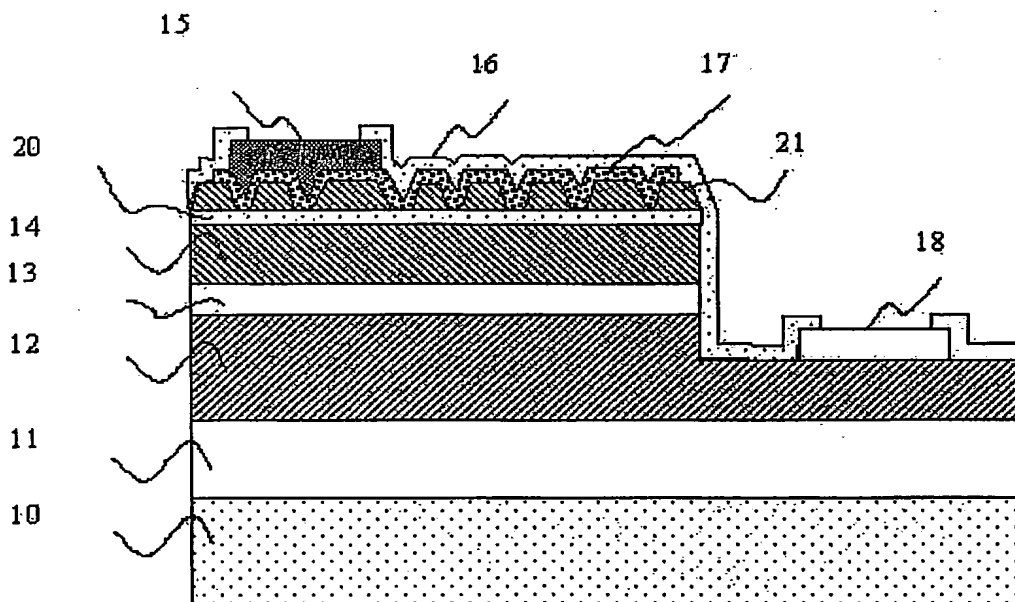
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**(54) Title:** III-NITRIDE COMPOUND EMICONDUCTOR LIGHT EMITTING DEVICE



**(57) Abstract:** The present invention relates a III-nitride compound semiconductor light emitting device in which a first layer composed of a carbon-containing compound layer, such as an n-type or p-type silicon carbide (SiC), silicon carbon nitride (SiCN) or carbon nitride layer (CN) layer, is formed on the p-type III-nitride semiconductor layer of the existing III-nitride semiconductor light emitting device, and a second layer composed of a III-nitride semiconductor layer with a given thickness is formed on the first layer.

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